

**C1200-30**

NIR LED CHIP

<Specifications>

Commodity Type and Physical Characteristics	
Material	InGaAsP/InP
Top Side P(anode)side	Au Alloy
Bottom Side N(cathode)side	Au Alloy
Electrode Pattern	Fig.1
Chip Size	Fig.2
Chip Thickness	Fig.2
Emission Area	Fig.2

Electro-Optical Characteristics[Ta=25°C]							
Item	Symbol	Condition	Min.	Typ.	Max.	Unit	
Forward Voltage	VF	IF=20mA		0.95	1.20	V	
		IF=50mA		1.00	1.30		
Reverse Current	IR	VR=3V			10	uA	
Power Intensity*	PO	IF=20mA		1.6		mW	
		IF=50mA		3.3			
Wavelength	Peak	$\lambda P$	IF=20mA	1150	1200	1250	nm
	Centroid	$\lambda C$	IF=20mA		1190		nm
Spectral Radiation Bandwidth	$\Delta\lambda$	IF=20mA		80		nm	
Rise Time	tr	IF=20mA		25		ns	
Fall Time	tf	IF=20mA		20		ns	

\* Measured by PD G8370-85

Die shall be mounted on TO-18 gold header without resin coated.

[Unit:um]

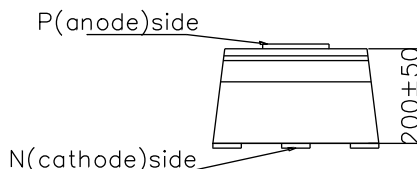
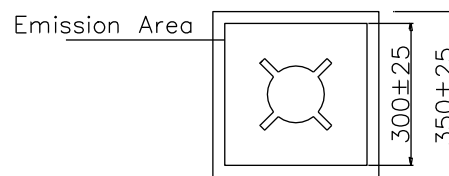
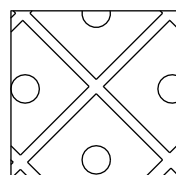
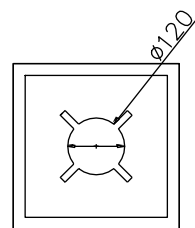


Fig.1 Electrode Pattern

Fig.2 Chip Size and Emission Area